

Schottky Barrier Diode

RB471E

●Applications

Low current rectification

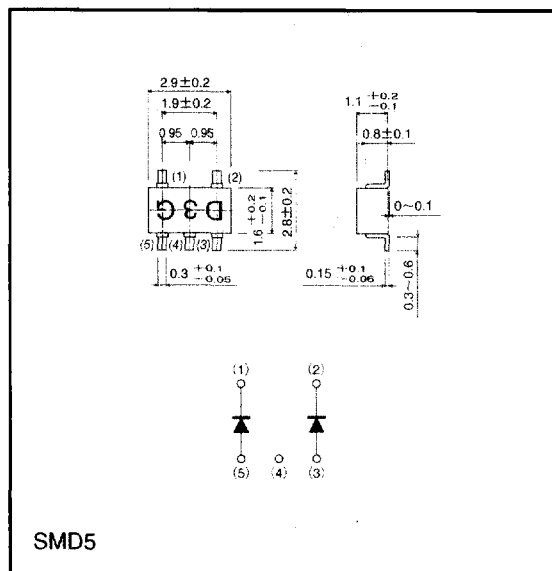
●Features

- 1) Designed for mounting on small surface areas (SMD5)
- 2) High reliability

●Construction

Silicon epitaxial

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	20	V
Peak reverse voltage	V_R	10	V
Mean rectifying current	I_o	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~125	°C

* 60 Hz for 1 ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.28	0.34	V	$I_F=10mA$
	V_{F2}	—	0.45	0.55	V	$I_F=100mA$
Reverse current	I_R	—	1	30	μA	$V_R=10V$
Capacitance between terminals	C_T	—	6.0	—	pF	$V_R=10V, 1MHz$

* Special precautions required concerning static electricity when being handled.

●Electrical characteristic curves (Ta=25°C)

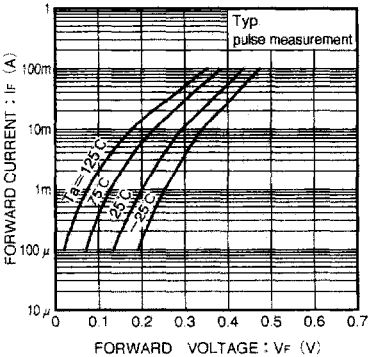


Fig. 1 Forward temperature characteristic

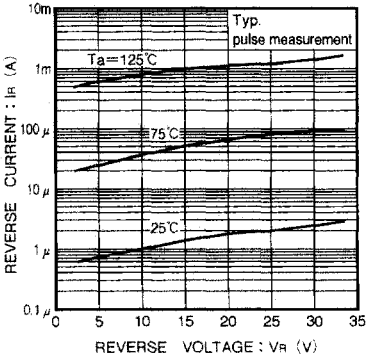


Fig. 2 Reverse temperature characteristic

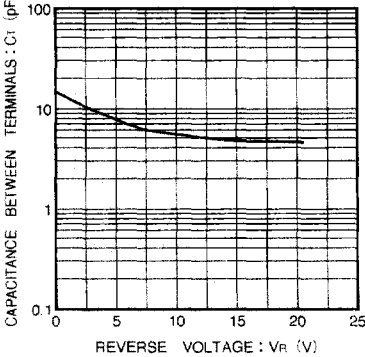


Fig. 3 Capacitance between terminals characteristic